NSN 5961-01-418-6113

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-418-6113 **Inclosure Material:** Metal **Overall Length:** 1.646 inches Overall Diameter: 0.544 inches **Mounting Facility Quantity: Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Overall Width Across Flats:** 0.563 inches **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** -5.0 peak gate voltage and 420.0 off-state voltage, rms total and 600.0 repetitive peak reverse voltage and 600.0 repetitive peak off-state voltage and 700.0 nonrepetitive peak reverse voltage and 700.0 nonrepetitive peak off-state voltage **Current Rating Per Characteristic:** 355.00 amperes peak forward surge current nanoamperes and 35.00 amperes forward current, total rms horsepower metric **Power Rating Per Characteristic:** 60.0 watts small-signal input power, common-collector blank and 1.0 watts small-signal input power, common-collector universal **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Test Data Document:** 53711-5906198 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 2 tab, solder lug and 1 threaded stud Shelf Life: N/a **Unit Of Measure: Demilitarization:** Yes - demil/mli Fiig: